

Darlington Transistors

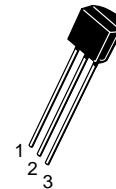
NPN Silicon

2N6426*
2N6427

*ON Semiconductor Preferred Device

MAXIMUM RATINGS

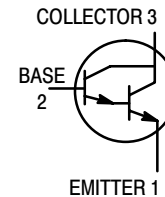
Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	40	Vdc
Collector–Base Voltage	V_{CBO}	40	Vdc
Emitter–Base Voltage	V_{EBO}	12	Vdc
Collector Current — Continuous	I_C	500	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	625 5.0	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.5 12	Watts mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$



CASE 29-04, STYLE 1
TO-92 (TO-226AA)

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	$^\circ\text{C}/\text{W}$



ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
----------------	--------	-----	-----	-----	------

OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage (1) ($I_C = 10 \text{ mAdc}, V_{BE} = 0$)	$V_{(BR)CEO}$	40	—	—	Vdc
Collector–Base Breakdown Voltage ($I_C = 100 \mu\text{Adc}, I_E = 0$)	$V_{(BR)CBO}$	40	—	—	Vdc
Emitter–Base Breakdown Voltage ($I_E = 10 \mu\text{Adc}, I_C = 0$)	$V_{(BR)EBO}$	12	—	—	Vdc
Collector Cutoff Current ($V_{CE} = 25 \text{ Vdc}, I_B = 0$)	I_{CES}	—	—	1.0	μAdc
Collector Cutoff Current ($V_{CB} = 30 \text{ Vdc}, I_E = 0$)	I_{CBO}	—	—	50	nAdc
Emitter Cutoff Current ($V_{EB} = 10 \text{ Vdc}, I_C = 0$)	I_{EBO}	—	—	50	nAdc

1. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$; Duty Cycle $\leq 2.0\%$.

2N6426 2N6427

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Typ	Max	Unit
ON CHARACTERISTICS					
DC Current Gain ⁽¹⁾ ($I_C = 10 \text{ mAdc}$, $V_{CE} = 5.0 \text{ Vdc}$)	h_{FE}	20,000	—	200,000	—
	2N6426	10,000	—	100,000	
	2N6427				
($I_C = 100 \text{ mAdc}$, $V_{CE} = 5.0 \text{ Vdc}$)		30,000	—	300,000	
	2N6426	20,000	—	200,000	
	2N6427				
($I_C = 500 \text{ mAdc}$, $V_{CE} = 5.0 \text{ Vdc}$)		20,000	—	200,000	
	2N6426	14,000	—	140,000	
	2N6427				
Collector–Emitter Saturation Voltage ($I_C = 50 \text{ mAdc}$, $I_B = 0.5 \text{ mAdc}$) ($I_C = 500 \text{ mAdc}$, $I_B = 0.5 \text{ mAdc}$)	$V_{CE(sat)}$	—	0.71	1.2	Vdc
		—	0.9	1.5	
Base–Emitter Saturation Voltage ($I_C = 500 \text{ mAdc}$, $I_B = 0.5 \text{ mAdc}$)	$V_{BE(sat)}$	—	1.52	2.0	Vdc
Base–Emitter On Voltage ($I_C = 50 \text{ mAdc}$, $V_{CE} = 5.0 \text{ Vdc}$)	$V_{BE(on)}$	—	1.24	1.75	Vdc

SMALL–SIGNAL CHARACTERISTICS

Output Capacitance ($V_{CB} = 10 \text{ Vdc}$, $I_E = 0$, $f = 1.0 \text{ MHz}$)	C_{obo}	—	5.4	7.0	pF
Input Capacitance ($V_{EB} = 1.0 \text{ Vdc}$, $I_C = 0$, $f = 1.0 \text{ MHz}$)	C_{ibo}	—	10	15	pF
Input Impedance ($I_C = 10 \text{ mAdc}$, $V_{CE} = 5.0 \text{ Vdc}$, $f = 1.0 \text{ kHz}$)	h_{ie}	100	—	2000	k Ω
	2N6426	50	—	1000	
	2N6427				
Small–Signal Current Gain ($I_C = 10 \text{ mAdc}$, $V_{CE} = 5.0 \text{ Vdc}$, $f = 1.0 \text{ kHz}$)	h_{fe}	20,000	—	—	—
	2N6426	10,000	—	—	
	2N6427				
Current–Gain — High Frequency ($I_C = 10 \text{ mAdc}$, $V_{CE} = 5.0 \text{ Vdc}$, $f = 100 \text{ MHz}$)	$ h_{fe} $	1.5	2.4	—	—
	2N6426	1.3	2.4	—	
	2N6427				
Output Admittance ($I_C = 10 \text{ mAdc}$, $V_{CE} = 5.0 \text{ Vdc}$, $f = 1.0 \text{ kHz}$)	h_{oe}	—	—	1000	μmhos
Noise Figure ($I_C = 1.0 \text{ mAdc}$, $V_{CE} = 5.0 \text{ Vdc}$, $R_S = 100 \text{ k}\Omega$, $f = 1.0 \text{ kHz}$)	NF	—	3.0	10	dB

1. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$; Duty Cycle $\leq 2.0\%$.

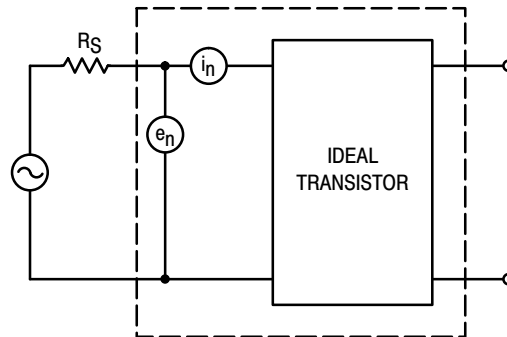


Figure 1. Transistor Noise Model

NOISE CHARACTERISTICS

($V_{CE} = 5.0 \text{ Vdc}$, $T_A = 25^\circ\text{C}$)

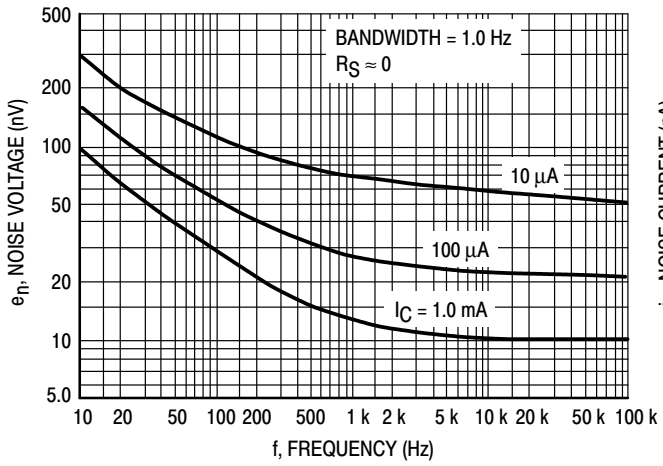


Figure 2. Noise Voltage

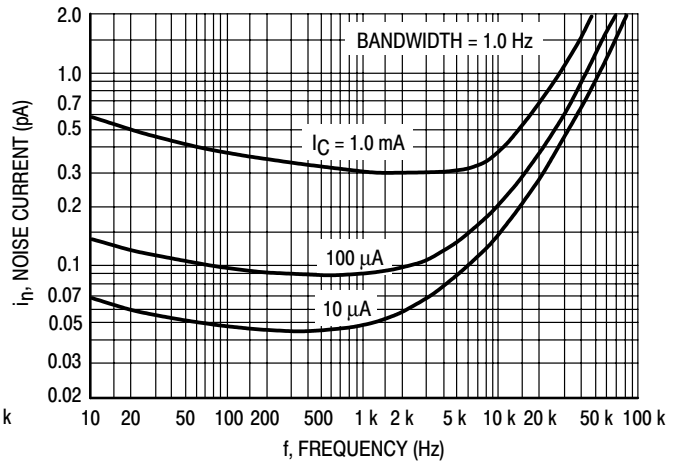


Figure 3. Noise Current

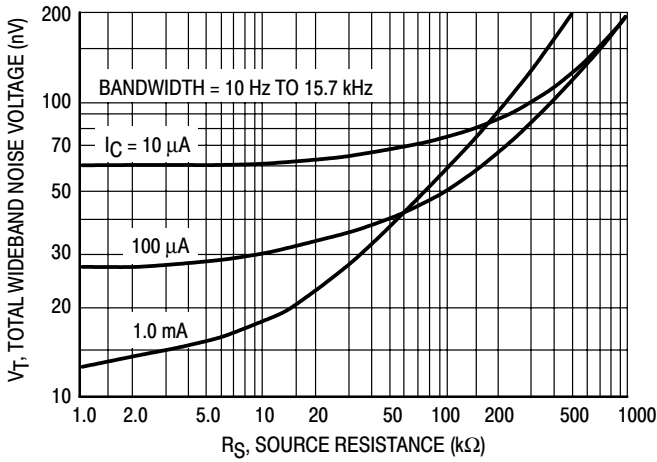


Figure 4. Total Wideband Noise Voltage

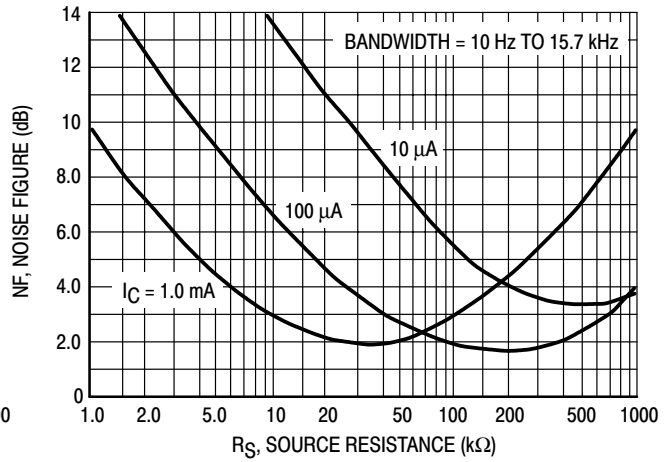


Figure 5. Wideband Noise Figure

SMALL-SIGNAL CHARACTERISTICS

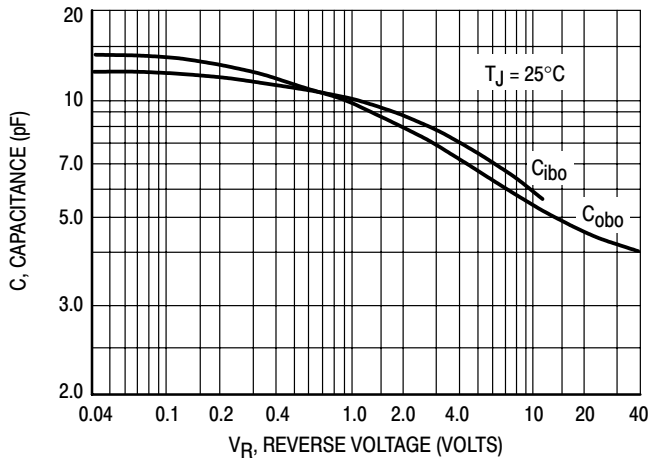


Figure 6. Capacitance

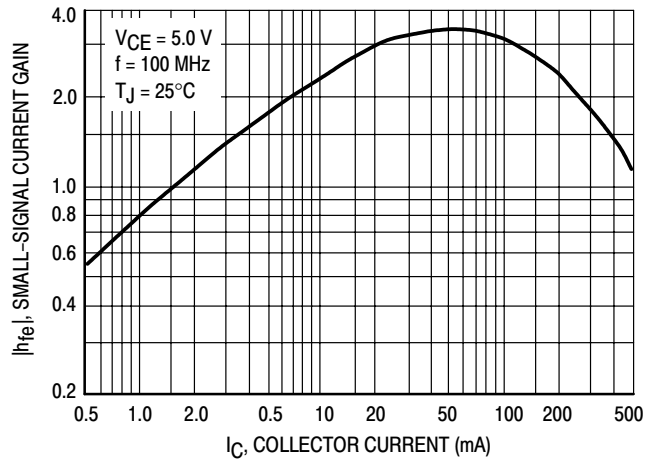


Figure 7. High Frequency Current Gain

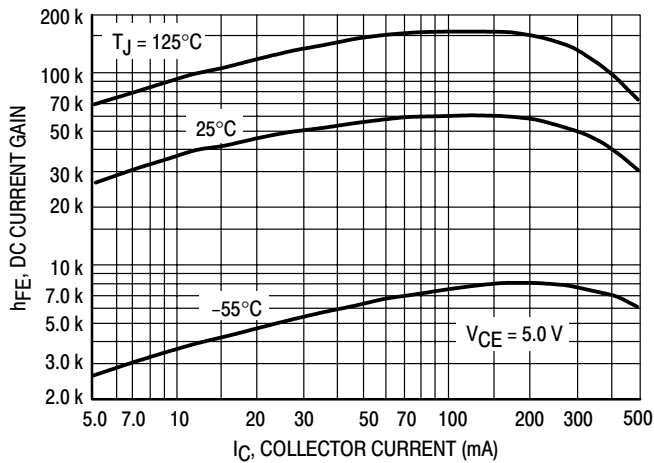


Figure 8. DC Current Gain

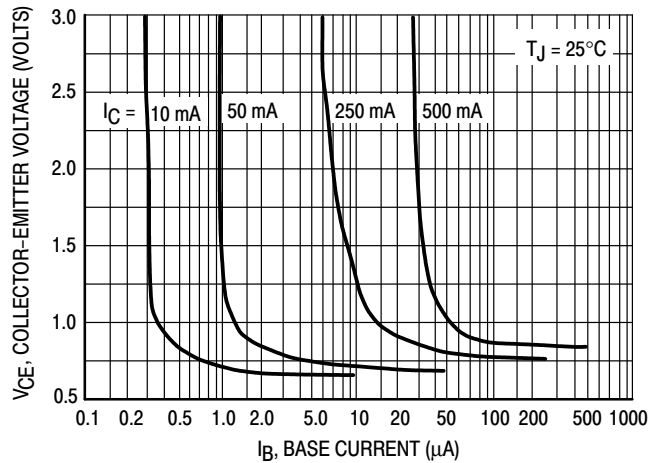


Figure 9. Collector Saturation Region

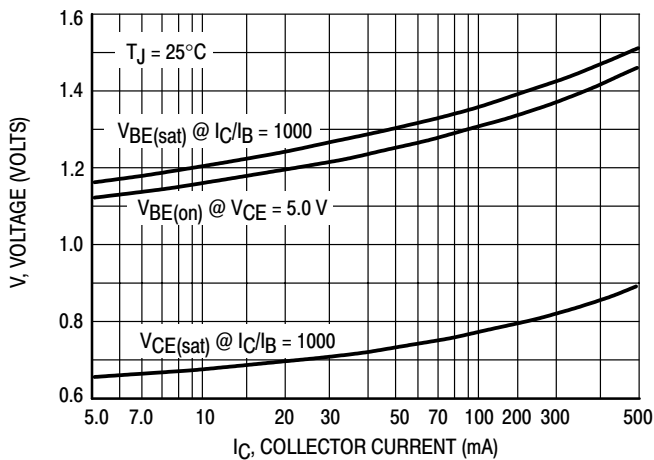


Figure 10. "On" Voltages

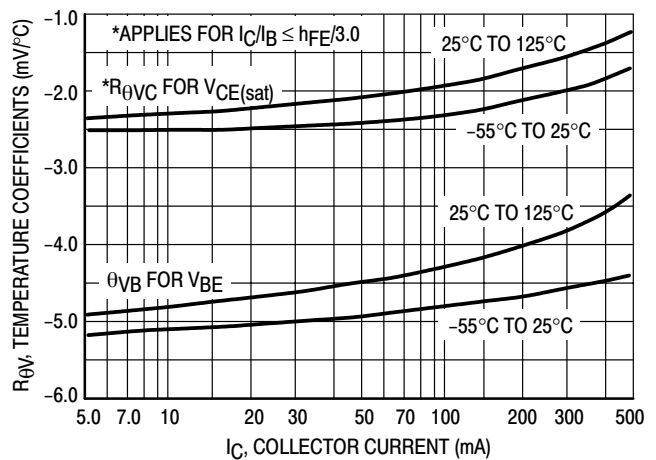


Figure 11. Temperature Coefficients

2N6426 2N6427

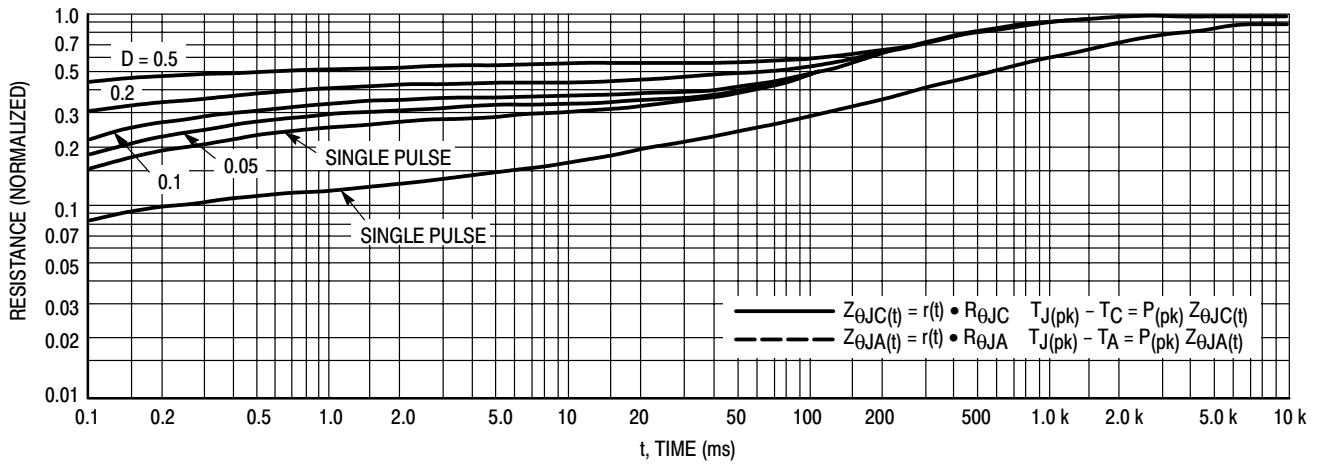


Figure 12. Thermal Response

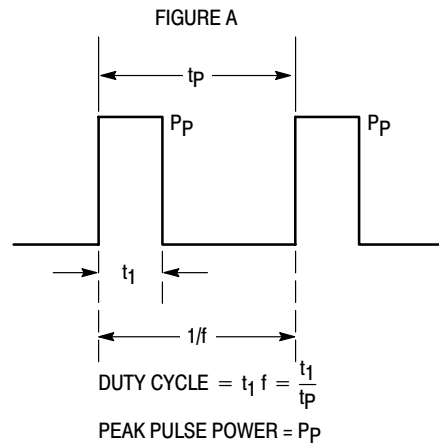
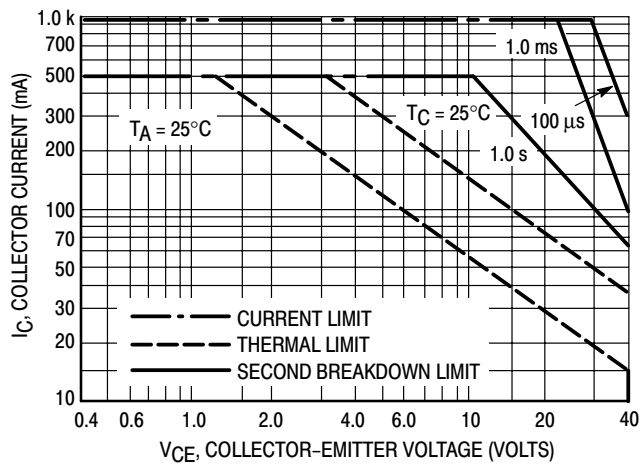
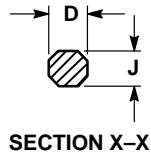
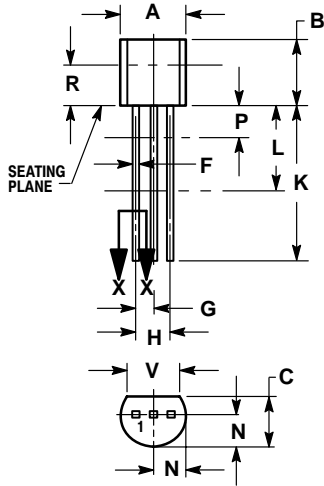


Figure 13. Active Region Safe Operating Area Design Note: Use of Transient Thermal Resistance Data

2N6426 2N6427

PACKAGE DIMENSIONS

CASE 029-04 (TO-226AA) ISSUE AD



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. DIMENSION F APPLIES BETWEEN P AND L. DIMENSION D AND J APPLY BETWEEN L AND K MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.022	0.41	0.55
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---

STYLE 1:

- PIN 1. EMITTER
2. BASE
3. COLLECTOR

Notes

ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer.

PUBLICATION ORDERING INFORMATION

Literature Fulfillment:

Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: ONlit@hibbertco.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

JAPAN: ON Semiconductor, Japan Customer Focus Center
4-32-1 Nishi-Gotanda, Shinagawa-ku, Tokyo, Japan 141-0031
Phone: 81-3-5740-2700
Email: r14525@onsemi.com

ON Semiconductor Website: <http://onsemi.com>

For additional information, please contact your local Sales Representative.